

J3 112. (Amended) The display device according to claim 110, wherein the laser annealing is performed to crystallize an amorphous semiconductor layer in order to obtain a crystalline semiconductor layer.

J4 115. (Amended) The display device according to claim 113, wherein the laser annealing is performed to crystallize an amorphous semiconductor layer in order to obtain a crystalline semiconductor layer.

J5 118. (Amended) The display device according to claim 116, wherein the laser annealing is performed to crystallize an amorphous semiconductor layer in order to obtain a crystalline semiconductor layer.

J6 121. (Amended) The display device according to claim 119, wherein the laser annealing is performed to crystallize an amorphous semiconductor layer in order to obtain a crystalline semiconductor layer.